



FORM PTO - 1449	ATTORNEY DOCKET NO.: ASC-044
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT	APPLICANT(S): Fitzgerald et al.
	SERIAL NO.: 09/884,172
	FILING DATE: June 19, 2001 GROUP: 2812 2822

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
E	A1	US 2002/0140031 A1	10/03/02	Rim	257	347	03/31/01
E	A2	US 2002/0125497 A1	09/12/02	Fitzgerald	257	191	07/16/01
E	A3	US 2002/0125471 A1	09/12/02	Fitzgerald et al.	257	19	12/04/01
E	A4	US 2002/0100942 A1	08/01/01	Fitzgerald et al.	257	369	06/19/01
E	A5	US 2001/0003364 A1	06/14/01	Sugawara et al.	257	192	12/08/00
E	A6	6,407,406	06/18/2002	Tezuka	257	18	06/29/1999
E	A7	6,399,970 B2	06/04/2002	Kubo et al.	257	194	09/16/97
E	A8	6,350,993	02/26/02	Chu et al.	257	19	03/12/99
E	A9	6,339,232	01/15/02	Takagi	257	192	09/20/99
E	A10	6,316,301	11/13/01	Kant	438	197	03/08/00
E	A11	6,291,321	09/08/01	Fitzgerald	438	494	03/09/99
E	A12	6,266,278	07/24/01	Harari et al.	365	185.18	08/08/00
E	A13	6,251,755	06/26/01	Furukawa et al.	438	510	04/22/99
E	A14	6,249,022	06/19/01	Lin et al.	257	324	10/22/99
E	A15	6,207,977	03/27/01	Augusto	257	192	10/21/98
E	A16	6,204,529	03/20/01	Lung et al.	257	314	08/27/99
E	A17	6,143,636	11/07/00	Forbes et al.	438	587	08/20/98
E	A18	6,130,453	10/10/00	Mei et al.	257	315	01/04/99
E	A19	6,117,750	09/12/00	Bensahel et al.	438	478	12/21/98
E	A20	6,111,267	08/29/00	Fishcher et al.			05/04/98
E	A21	6,107,653	08/22/2000	Fitzgerald	257	191	06/23/1998
E	A22	6,096,590	08/01/00	Chan et al.	438	233	06/30/98
E	A23	6,058,044	05/02/00	Sugiura et al.	365	185.17	12/09/98

EXAMINER

Christopher L. Linn

DATE CONSIDERED

6/2/03



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<u>E</u>	A24	5,998,807	12/07/99	Lustig et al.	257	66	09/09/97
<u>E</u>	A25	5,963,817	10/05/99	Chu et al.	438	410	10/16/97
<u>C</u>	A26	5,912,479	06/15/99	Mori et al.	257	192	07/25/97
<u>E</u>	A27	5,891,769	04/06/99	Liaw et al.	438	167	02/27/98
<u>E</u>	A28	5,847,419	12/08/98	Imai et al.	257	192	09/16/97
<u>E</u>	A29	5,792,679	08/11/98	Nakato	438	162	08/30/93
<u>E</u>	A30	5,786,612	07/28/98	Otani et al.	257	316	04/16/96
<u>E</u>	A31	5,739,567	04/14/98	Wong	257	316	11/08/94
<u>E</u>	A32	5,698,869	12/16/97	Yoshim et al.	257	192	09/13/95
<u>E</u>	A33	5,683,934	11/04/97	Candelaria	437	134	05/03/96
<u>E</u>	A34	5,617,351	04/01/97	Bertin et al.	365	185.05	06/05/95
<u>E</u>	A35	5,596,527	01/21/97	Tomioka et al.	365	185.2	02/13/95
<u>E</u>	A36	5,523,592	06/04/96	Nakagawa et al.	257	96	02/01/94
<u>E</u>	A37	5,523,243	06/04/96	Mohammad	437	31	06/08/94
<u>E</u>	A38	5,479,033	12/26/95	Baca et al.	257	192	05/27/94
<u>E</u>	A39	5,461,250	10/24/95	Burghartz et al.	257	347	08/10/92
<u>E</u>	A40	5,442,205	08/15/95	Brasen et al.	257	191	08/09/93
<u>E</u>	A41	5,426,316	06/20/95	Mohammad	257	197	06/08/94
<u>E</u>	A42	5,316,958	05/31/94	Meyerson	437	31	05/31/90
<u>E</u>	A43	5,291,439	03/01/94	Kauffmann et al.	365	185	09/12/91
<u>E</u>	A44	5,155,571	10/13/1992	Wang et al.	357	47	08/06/1990
<u>E</u>	A45	4,990,979	02/05/91	Otto	357	23.5	04/27/89

FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUN TRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTR ACT ONLY	ENGLISH LANG (Y/N)
<u>E</u>	B1	41 01 167 A1	07/23/92	DE				No	Yes (abstract only)
EXAMINER <i>Christopher L. Lottin</i>					DATE CONSIDERED <i>6/2/03</i>				



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					FILING DATE: June 19, 2001		GROUP: ²⁸¹² 2822	
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EXAMINER <i>Christopher J. Fathin</i>				DATE CONSIDERED <i>6/2/03</i>				



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OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
E	C1	"2 Bit/Cell EEPROM Cell Using Band to Band Tunneling for Data Read-Out," <u>IBM Technical Disclosure Bulletin</u> , Vol. 35, No. 4B (September 1992) pp. 136-140.
E	C2	Armstrong et al., "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEDM Technical Digest</u> (1995 International Electron Devices Meeting) pp. 761-764.
E	C3	Barradas et al., "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMOS transistors," <u>Modern Physics Letters B</u> (2001) (abstract).
E	C4	Bouillon et al., "Search for the optimal channel architecture for 0.18/0.12 μm bulk CMOS Experimental study," <u>IEEE</u> , (1996) pp. 21.2.1-21.2.4.
E	C5	Bufler et al., "Hole transport in strained $\text{Si}_{1-x}\text{Ge}_x$ alloys on $\text{Si}_{1-y}\text{Ge}_y$ substrates," <u>Journal of Applied Physics</u> , Vol. 84, No. 10 (November 15, 1998) pp. 5597-5602.
E	C6	Canaperi et al., "Preparation of a relaxed Si-Ge layer on an insulator in fabricating high-speed semiconductor devices with strained epitaxial films," <u>International Business Machines Corporation</u> , USA (2002) (abstract).
E	C7	Carlin et al., "High Efficiency GaAs-on-Si Solar Cells with High V_{oc} Using Graded GeSi Buffers," <u>IEEE</u> (2000) pp. 1006-1011
E	C8	Cheng et al., "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," <u>IEEE Electron Device Letters</u> , Vol. 22, No. 7 (July 2001) pp. 321-323.
E	C9	Cheng et al., "Relaxed Silicon-Germanium on Insulator Substrate by Layer Transfer," <u>Journal of Electronic Materials</u> , Vol. 30, No. 12 (2001) pp. L37-L39.
E	C10	Cullis et al., "Growth ripples upon strained SiGe epitaxial layers on Si and misfit dislocation interactions," <u>Journal of Vacuum Science and Technology A</u> , Vol. 12, No. 4 (July/August 1994) pp. 1924-1931.
E	C11	Currie et al., "Carrier mobilities and process stability of strained S in- and p-MOSFETs on SiGe virtual substrates," <u>J. Vac. Sci. Technol. B</u> , Vol. 19, No. 6 (Nov/Dec 2001) pp. 2268-2279.
E	C12	Currie et al., "Controlling threading dislocation densities in Ge on Si using graded SiGe layers and chemical-mechanical polishing," <u>Applied Physics Letters</u> , Vol. 72, No. 14 (April 6, 1998) pp 1718-1720.
E	C13	Eaglesham et al., "Dislocation-Free Stranski-Krastanow Growth of Ge on Si(100)," <u>Physical Review Letters</u> , Vol. 64, No. 16 (April 16, 1990) pp. 1943-1946.
E	C14	Fischetti et al., "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys," <u>J. Appl. Phys.</u> , Vol. 80, No. 4 (August 15, 1996) pp. 2234-2252.
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	6/2/03	



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	C15	Fischetti, "Long-range Coulomb interactions in small Si devices. Part II. Effective electronmobility in thin-oxide structures," <u>Journal of Applied Physics</u> , Vol. 89, No. 2 (January 15, 2001) pp. 1232-1250.
	C16	Fitzgerald et al., "Relaxed Ge _x Si _{1-x} structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," <u>J. Vac. Sci. Technol. B</u> , Volume 10, No. 4 (July/August 1992) pp. 1807-1819.
	C17	Fitzgerald et al., "Dislocation dynamics in relaxed graded composition semiconductors," <u>Materials Science and Engineering B67</u> , (1999) pp. 53-61.
	C18	Fitzgerald et al., "Totally relaxed Ge _x Si _{1-x} layers with low threading dislocation densities grown on Si substrates," <u>Appl. Phys. Lett.</u> , Vol. 59, No. 7 (August 12, 1991) pp. 811-813.
	C19	Garone et al., "Silicon vapor phase epitaxial growth catalysis by the presence of germane," <u>Applied Physics Letters</u> , Vol. 56, No. 13 (March 26, 1990) pp. 1275-1277.
	C20	Grützmacher et al., "Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere," <u>Applied Physics Letters</u> , Vol. 63, No. 18 (November 1, 1993) pp. 2531-2533.
	C21	Hackbarth et al., "Alternatives to thick MBE-grown relaxed SiGe buffers," <u>Thin Solid Films</u> , Vol. 369, (2000) pp. 148-151.
	C22	Hackbarth et al., "Strain relieved SiGe buffers for Si-based heterostructure field-effect transistors," <u>Journal of Crystal Growth</u> , Vol. 201/202 (1999) pp. 734-738.
	C23	Herzog et al., "SiGe-based FETs: buffer issues and device results," <u>Thin Solid Films</u> , Vol. 380 (2000) pp. 36-41.
	C24	Höck et al., "Carrier mobilities in modulation doped Si _{1-x} Ge _x heterostructures with respect to FET applications," <u>Thin Solid Films</u> , Vol. 336 (1998) pp. 141-144.
	C25	Höck et al., "High hole mobility in Si _{0.17} Ge _{0.83} channel metal-oxide-semiconductor field-effect transistors grown by plasma-enhanced chemical vapor deposition," <u>Applied Physics Letters</u> , Volume 76, No. 26 (June 26, 2000) pp. 3920-3922.
	C26	Höck et al., "High performance 0.25 µm p-type Ge/SiGe MODFETs," <u>Electronics Letters</u> , Vol. 34, No. 19 (September 17, 1998) pp. 1888-1889.
	C27	Ismail et al., "Modulation-doped n-type Si/SiGe with inverted interface," <u>Appl. Phys. Lett.</u> , Vol. 65, No. 10 (September 5, 1994) pp. 1248-1250.
	C28	Kearney et al., "The effect of alloy scattering on the mobility of holes in a Si _{1-x} Ge _x quantum well," <u>Semicond. Sci Technol.</u> , Vol. 13 (1998) pp. 174-180.
	C29	Koester et al., "Extremely High Transconductance Ge/Si _{0.4} Ge _{0.6} p-MODFET's Grown by UHV-CVD," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 3 (March 2000) pp. 110-112.
	C30	Konig et al., "Design Rules for n-type SiGe Hetero FETs," <u>Solid-State Electronics</u> , Vol. 41, No. 10 (1997) pp. 1541-1547.
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E	C31	König et al., "p-Type Ge-Channel MODFET's with High Transconductance Grown on Si Substrates," <u>IEEE Electron Device Letters</u> , Vol. 14, No. 4 (April 1993) pp. 205-207.
E	C32	König et al., "SiGe HBTs and HFETs," <u>Solid-State Electronics</u> , Vol. 38, No. 9 (1995) pp. 1595-1602.
E	C33	Lee et al., "Strained Ge channel p-type metal-oxide-semiconductor field-effect transistors grown on Si _{1-x} Ge _x /Si virtual substrates," <u>Applied Physics Letters</u> , Vol. 79, No. 20 (November 12, 2001) pp. 3344-3346.
E	C34	Lee et al., "Strained Ge channel p-type MOSFETs fabricated on Si _{1-x} Ge _x /Si virtual substrates," <u>Mat. Res. Soc. Symp. Proc.</u> , Vol. 686 (2002) pp. A1.9.1-A1.9.5.
E	C35	Leitz et al., "Channel Engineering of SiGe-Based Heterostructures for High Mobility MOSFETs," <u>Mat. Res. Soc. Symp. Proc.</u> , Vol. 686 (2002) pp. A3.10.1-A3.10.6.
E	C36	Leitz et al., "Dislocation glide and blocking kinetics in compositionally graded SiGe/Si," <u>Journal of Applied Physics</u> , Vol. 90, No. 6 (September 15, 2001) pp. 2730-2736.
E	C37	Leitz et al., "Hole mobility enhancements in strained Si/Si _{1-y} Ge _y p-type metal-oxide-semiconductor field-effect transistors grown on relaxed Si _{1-x} Ge _x (x<y) virtual substrates," <u>Applied Physics Letters</u> , Vol. 79, No. 25 (December 17, 2001) pp. 4246-4248.
E	C38	Li et al., "Design of high speed Si/SiGe heterojunction complementary metal-oxide-semiconductor field effect transistors with reduced short-channel effects," <u>J. Vac. Sci. Technol.</u> , A Vol. 20 No.3 (May/June 2002) pp. 1030-1033.
E	C39	Maiti et al., "Strained-Si Heterostructure Field Effect Transistors," <u>Semiconductor Science and Technology</u> , Vol. 13 (1998) pp. 1225-1246.
E	C40	Meyerson et al., "Cooperative Growth Phenomena in Silicon/Germanium Low-Temperature Epitaxy," <u>Applied Physics Letters</u> , Vol. 53, No. 25 (December 19, 1988) pp. 2555-2557.
E	C41	Mizuno et al., "High Performance Strained-Si p-MOSFETs on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology," <u>IEEE IDEM Technical Digest</u> , (1999 International Electron Device Meeting) pp. 934-936.
E	C42	Mizuno, "Advanced SOI-MOSFETs with Strained-Si Channel for High Speed CMOS - Electron/Hole Mobility Enhancement" 2000 Symposium on VLSI Technology, Digest of Technical Papers, Honolulu (June 13-15 2000), IEEE NY, NY, pp. 210-211.
E	C43	O'Neill et al., "SiGe Virtual substrate N-channel heterojunction MOSFETS," <u>Semicond. Sci. Technol.</u> , Vol. 14 (1999) pp. 784-789.
E	C44	Parker et al., "SiGe heterostructure CMOS circuits and applications," <u>Solid State Electronics</u> , Vol. 43 (1999) pp. 1497-1506.
E	C45	Ransom et al., "Gate-Self-Aligned n-channel and p-channel Germanium MOSFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 38, No. 12 (December 1991) pp. 2695.
E	C46	Reinking et al., "Fabrication of high-mobility Ge p-channel MOSFETs on Si substrates," <u>Electronics Letters</u> , Vol. 35, No. 6 (March 18, 1999) pp. 503-504.
E	C47	Robbins et al., "A model for heterogeneous growth of Si _{1-x} Ge _x films for hydrides," <u>Journal of Applied Physics</u> , Vol. 69, No. 6 (March 15, 1991) pp. 3729-3732.
EXAMINER <i>Christy Latta</i>		DATE CONSIDERED 6/13/03



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E	C48	Sadek et al., "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEEE Transactions on Electron Devices</u> , Vol. 43, No. 8 (August 1996) pp. 1224-1232.
E	C49	Schäffler, "High-Mobility Si and Ge Structures," <u>Semiconductor Science and Technology</u> , Vol. 12 (1997) pp. 1515-1549.
E	C50	Tweet et al., "Factors determining the composition of strained GeSi layers grown with disilane and germane," <u>Applied Physics Letters</u> , Vol. 65, No. 20 (November 14, 1994) pp. 2579-2581.
E	C51	Usami et al., "Spectroscopic study of Si-based quantum wells with neighboring confinement structure," <u>Semicon. Sci. Technol.</u> (1997) (abstract).
E	C52	Welser et al., "Electron Mobility Enhancement in Strained-Si N-Type Metal-Oxide-Semiconductor Field-Effect Transistors," <u>IEEE Electron Device Letters</u> , Vol. 15, No. 3 (March 1994) pp. 100-102.
E	C53	Welser et al., "Evidence of Real-Space Hot-Electron Transfer in High Mobility, Strained-Si Multilayer MOSFETs," <u>IEEE IDEM Technical Digest</u> (1993 International Electron Devices Meeting) pp. 545-548.
E	C54	Welser et al., "NMOS and PMOS Transistors Fabricated in Strained Silicon/Relaxed Silicon-Germanium Structures," <u>IEEE IDEM Technical Digest</u> (1992 International Electron Devices Meeting) pp. 1000-1002.
E	C55	Xie et al., "Semiconductor Surface Roughness: Dependence on Sign and Magnitude of Bulk Strain," <u>The Physical Review Letters</u> , Vol. 73, No. 22 (November 28, 1994) pp. 3006-3009.
E	C56	Xie et al., "Very high mobility two-dimensional hole gas in Si/Ge _x Si _{1-x} /Ge structures grown by molecular beam epitaxy," <u>Appl. Phys. Lett.</u> , Vol. 63, No. 16 (October 18, 1993) pp. 2263-2264.
E	C57	Xie, "SiGe Field effect transistors," <u>Materials Science and Engineering</u> , Vol. 25 (1999) pp. 89-121.
E	C58	International Search Report for International Application No. PCT/US01/46322 mailed January 22, 2003.
EXAMINER <i>Christopher Patton</i>		DATE CONSIDERED <i>6/3/03</i>